

	Type	Hits	S arch Text	DBs	Time Stamp
1	BRS	3508	trench adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/25 14:41
2	BRS	1445	((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:32
3	BRS	342	collar adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:33
4	BRS	571	node adj dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:33
5	BRS	0	buried adj diffusion adj plate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:33
6	BRS	2923	pad adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:33
7	BRS	0	((trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon)) and (collar adj oxide) and (node adj dielectric) and (pad adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:34
8	BRS	121	((trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:34
9	BRS	15	((trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon)) and (node adj dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:34
10	BRS	0	((trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon)) and (node adj dielectric) and (pad adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:35
11	BRS	16	((trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon)) and (collar adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:35
12	BRS	5	((trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon)) and (pad adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:43

	Type	Hits	Search Text	DBs	Time Stamp
13	BRS	9	(trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon)) and (collar adj oxide) and (node adj dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:43
14	BRS	2	(trench adj capacitor) and ((first adj polysilicon) and (second adj polysilicon) and (third adj polysilicon)) and (collar adj oxide) and (pad adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 12:44
15	BRS	0	"10604287"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/23 13:05
16	BRS	2	6472702.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/28 13:33
17	BRS	131	node with ONO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/25 14:41
18	BRS	16	(trench adj capacitor) and (node with ONO)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/25 14:42
19	BRS	32	photoresist same sacrificial	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/25 14:42
20	BRS	0	(trench adj capacitor) and (photoresist same sacrificial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/25 14:42
21	BRS	2	capacitor and (photoresist same sacrificial)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/25 14:42